

**Features**

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Green Device Available

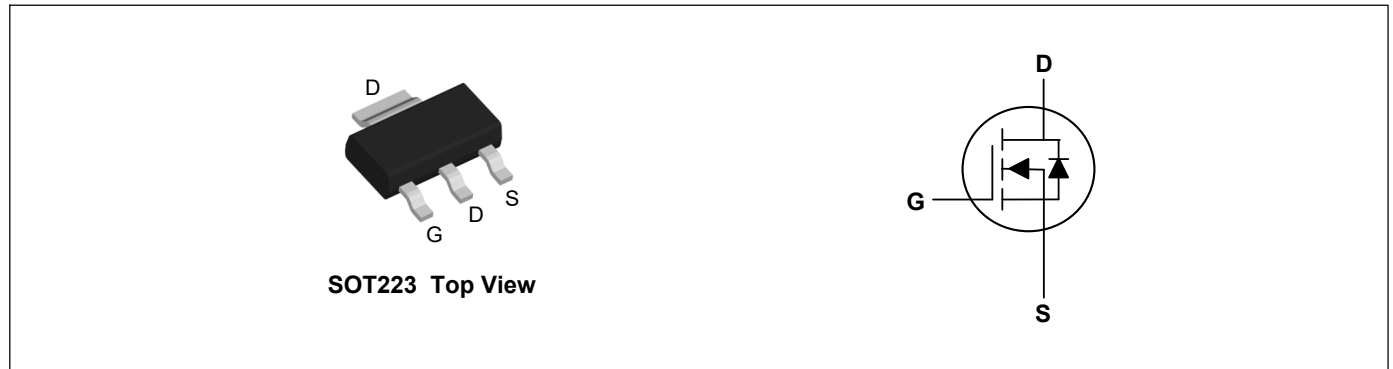
**Product Summary**



$V_{DS}$	100	V
$I_D$	3	A
$R_{DS(ON)}$ (at $V_{GS}=10V$ )	75	m $\Omega$
$R_{DS(ON)}$ (at $V_{GS}=4.5V$ )	82	m $\Omega$

**Applications**

- High Frequency Point-of-Load, Synchronous Buck Converter
- Networking DC-DC Power System
- Load Switch



**Absolute Maximum Ratings( $T_A=25^{\circ}C$ , unless otherwise noted)**

Parameter	Symbol	Rating	Units
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current, $V_{GS}$ @ 10V <sup>1</sup>	$I_D@T_A=25^{\circ}C$	3	A
Continuous Drain Current, $V_{GS}$ @ 10V <sup>1</sup>	$I_D@T_A=70^{\circ}C$	2.4	A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	15	A
Total Power Dissipation <sup>3</sup>	$P_D@T_A=25^{\circ}C$	2	W
Storage Temperature Range	$T_{STG}$	-55 to 150	$^{\circ}C$
Operating Junction Temperature Range	$T_J$	-55 to 150	$^{\circ}C$

**Thermal Characteristics**

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Ambient <sup>1</sup>	$R_{\theta JA}$	---	85	$^{\circ}C/W$
Thermal Resistance Junction-Case <sup>1</sup>	$R_{\theta JC}$	---	24	$^{\circ}C/W$

**Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	100	---	---	V
BV <sub>DSS</sub> Temperature Coefficient	ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Reference to 25°C, I <sub>D</sub> =1mA	---	0.082	---	V/°C
Static Drain-Source On-Resistance <sup>2</sup>	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =3A	---	60	75	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =2A	---	65	82	mΩ
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.2	---	2.5	V
V <sub>GS(th)</sub> Temperature Coefficient	ΔV <sub>GS(th)</sub>		---	-4.8	---	mV/°C
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =80V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	-1	uA
		V <sub>DS</sub> =80V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	-5	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =3A	---	5.8	---	S
Gate Resistance	R <sub>g</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	1.4	2.8	Ω
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =80V, V <sub>GS</sub> =10V, I <sub>D</sub> =3A	---	40	---	nC
Gate-Source Charge	Q <sub>gs</sub>		---	7.3	---	
Gate-Drain Charge	Q <sub>gd</sub>		---	7	---	
Turn-On Delay Time	T <sub>d(on)</sub>	V <sub>DD</sub> =50V, V <sub>GS</sub> =10V, R <sub>G</sub> =3.3Ω, I <sub>D</sub> =3A	---	9.2	---	ns
Rise Time	T <sub>r</sub>		---	22	---	
Turn-Off Delay Time	T <sub>d(off)</sub>		---	41	---	
Fall Time	T <sub>f</sub>		---	19.6	---	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz	---	2400	---	pF
Output Capacitance	C <sub>oss</sub>		---	100	---	
Reverse Transfer Capacitance	C <sub>rss</sub>		---	82	---	

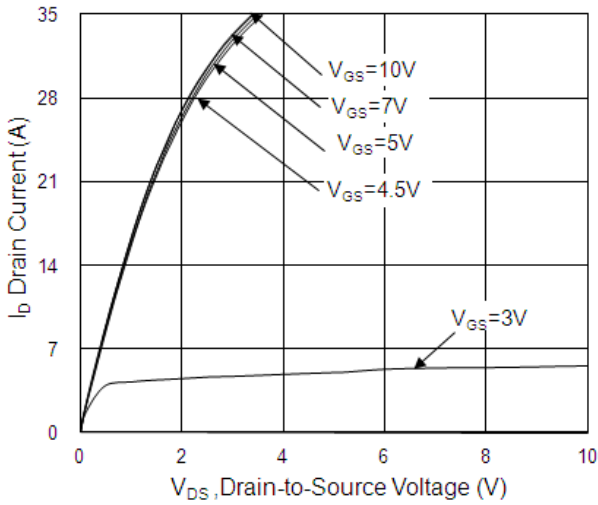
**Drain-Source Diode Characteristics**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Continuous Source Current <sup>1,4</sup>	I <sub>S</sub>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	3	A
Pulsed Source Current <sup>2,4</sup>	I <sub>SM</sub>		---	---	15	A
Diode Forward Voltage <sup>2</sup>	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1.2	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> =3A, di/dt=100A/μs, T <sub>J</sub> =25°C	---	41	---	nS
Reverse Recovery Charge	Q <sub>rr</sub>		---	25	---	nC

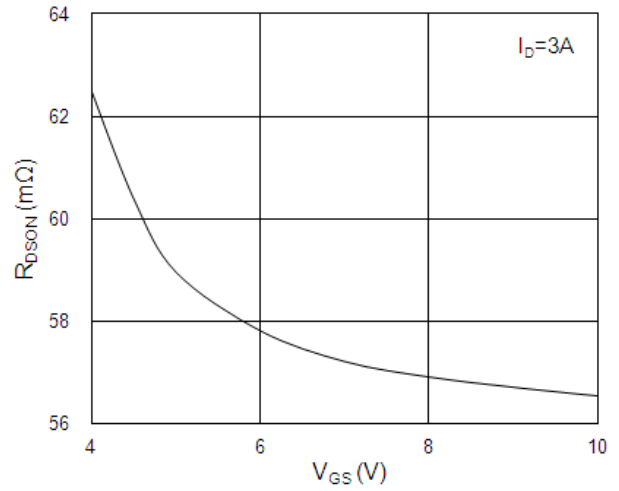
**Note:**

- The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- The power dissipation is limited by 150°C junction temperature
- The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.

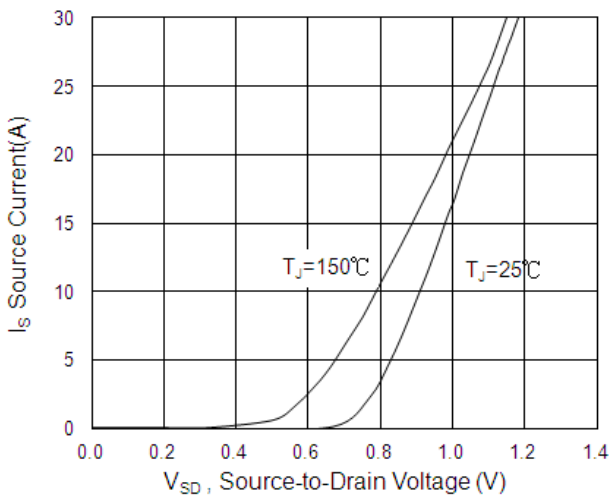
**Typical Characteristics**



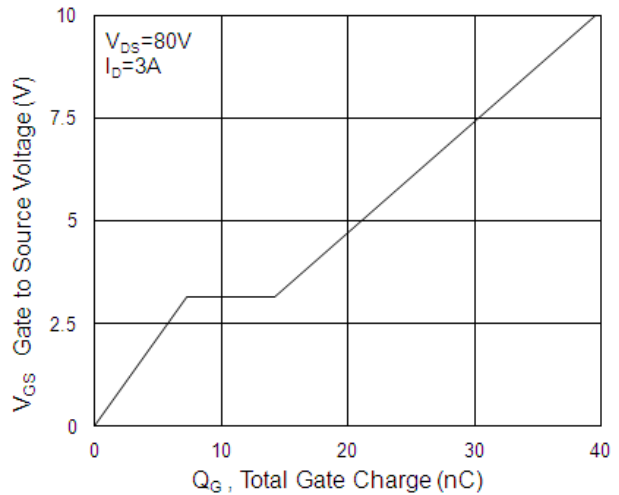
**Fig.1 Typical Output Characteristics**



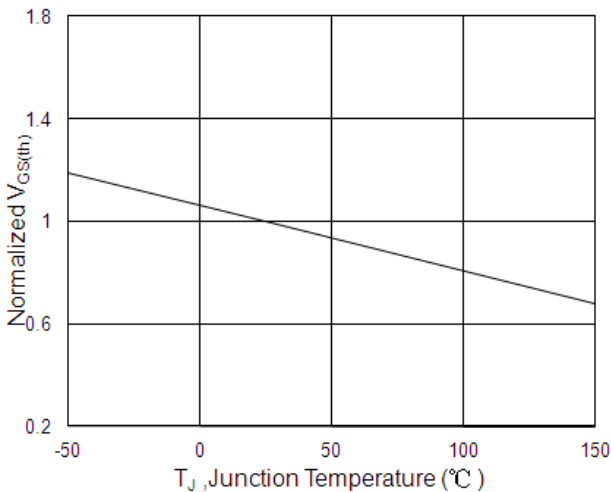
**Fig.2 On-Resistance vs. Gate-Source**



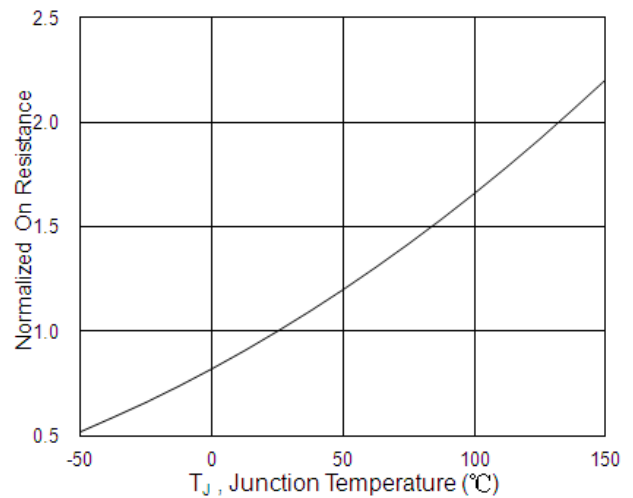
**Fig.3 Forward Characteristics of Reverse**



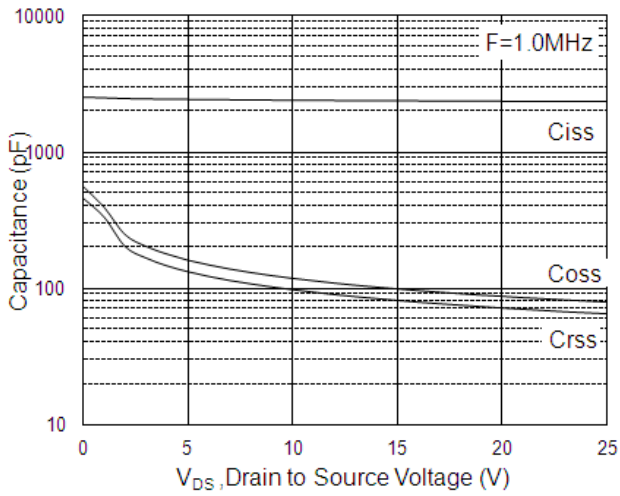
**Fig.4 Gate-Charge Characteristics**



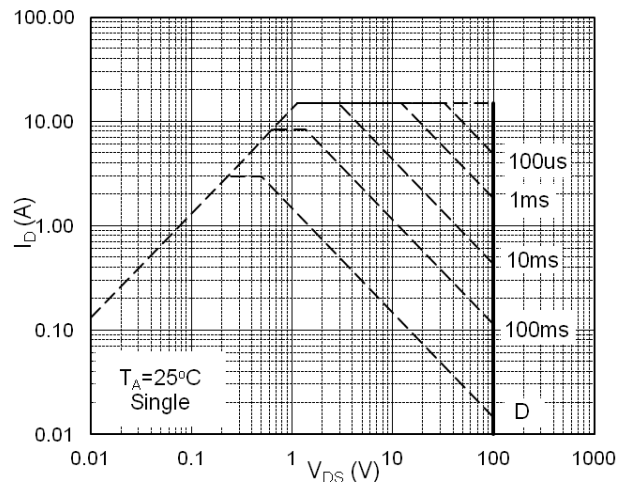
**Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$**



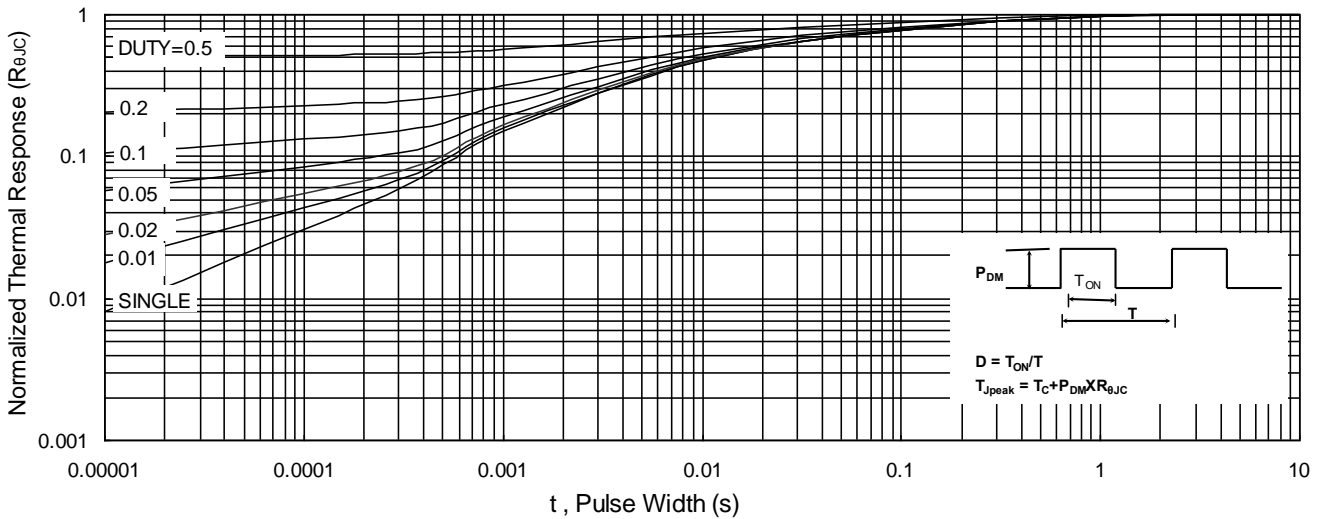
**Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$**



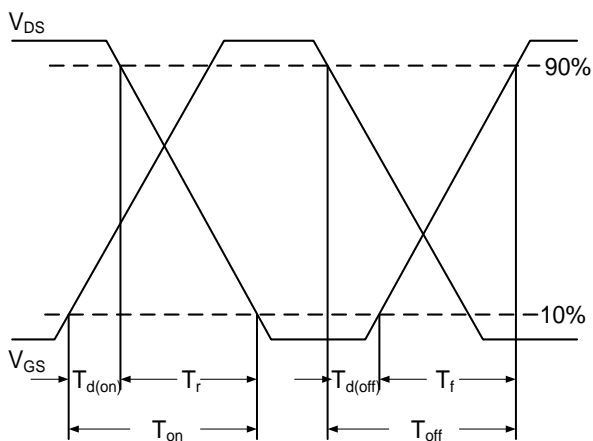
**Fig.7 Capacitance**



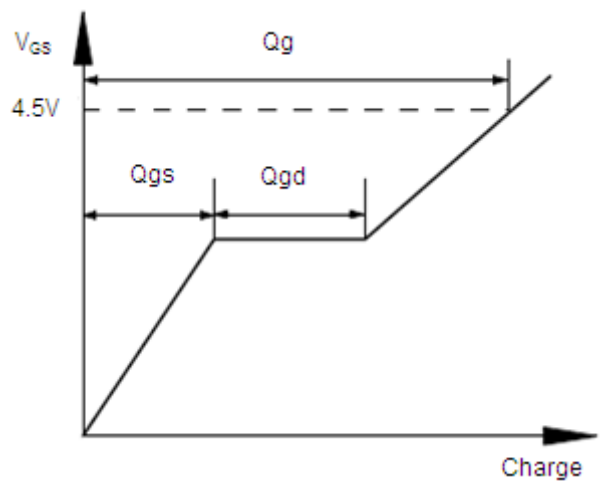
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**

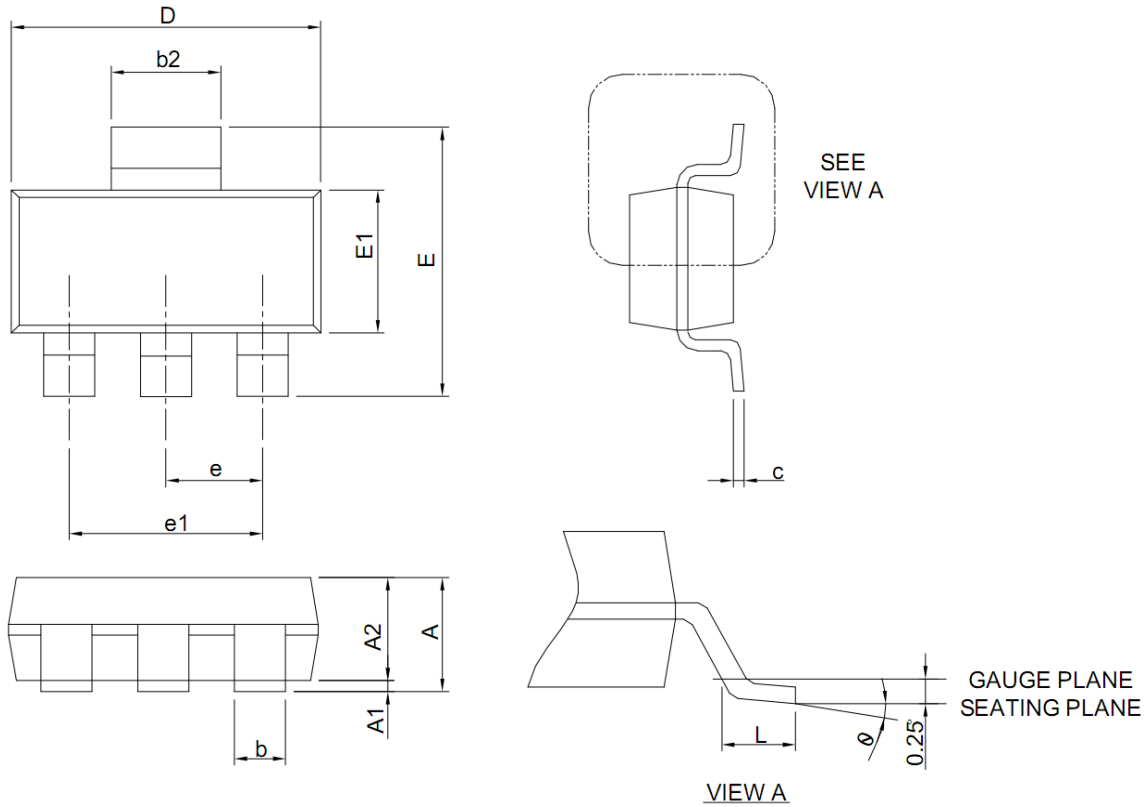


**Fig.10 Switching Time Waveform**



**Fig.11 Gate Charge Waveform**

**SOT223 Package Outline Dimensions**



Symbol	Dimensions (unit:mm)			Symbol	Dimensions (unit:mm)		
	Min	Typ	Max		Min	Typ	Max
<b>A</b>	1.50	1.65	1.80	<b>A1</b>	0.02	0.06	0.10
<b>A2</b>	1.50	1.60	1.70	<b>b</b>	0.66	0.72	0.80
<b>b2</b>	2.90	3.00	3.10	<b>c</b>	0.23	0.30	0.35
<b>D</b>	6.30	6.50	6.70	<b>E</b>	6.70	7.00	7.30
<b>E1</b>	3.30	3.50	3.70	<b>e</b>	2.30 REF		
<b>e1</b>	4.60 REF			<b>L</b>	0.75	--	1.15
<b><math>\theta</math></b>	0°	--	10°				